

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-243263

(43)Date of publication of application : 31.08.1992

(51)Int.Cl.

G03F 7/38
G03F 7/36
H01L 21/027
H01L 21/302

(21)Application number : 03-004595

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(22)Date of filing : 18.01.1991

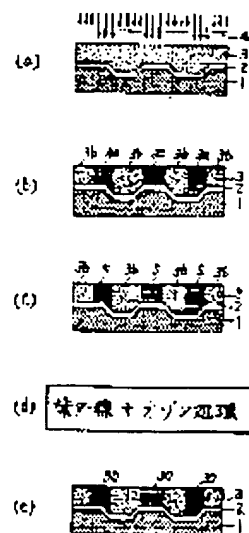
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(54) FINE PATTERN FORMING METHOD

(57)Abstract:

PURPOSE: To conduct the etching being strong in the selectivity by performing the oxidation treatment on the sililated portion of the resist for dry development use by using preliminary ultraviolet ray and ozone.

CONSTITUTION: The resist 3 for dry development use is applied on a substrate 1 and the exposed portion 3a is sililated and subsequently is dry-developed. The sililated portion 5 of the resist 3 is preliminary carried out the oxidation treatment Namely while the resist 3 for dry development use is exposed to an ozone gas, the ozone gas is irradiated with light. Like this at the etching time with the reactive ions, when the oxygen ions having energy are irradiated, a stable oxidized film 30 against the oxygen ions has already been formed on the sililated portion 5. Then compared to the case that the oxygen ions are irradiated from the beginning, the etching of the sililated portion is hard to proceed.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the

✓ examiner's decision of rejection or application
converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of
rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

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